

## Silicon NPN Power Transistors

2SC4303

**DESCRIPTION**

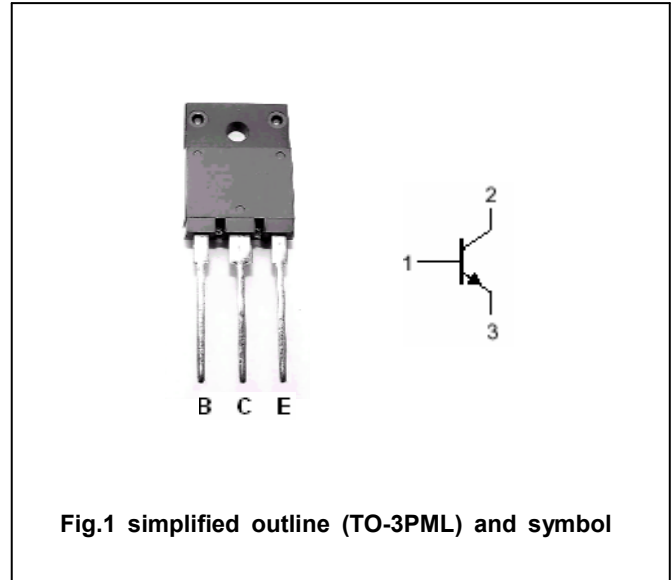
- With TO-3PML package
- High voltage switching transistor

**APPLICATIONS**

- Switching Regulator,
- Lighting Inverter and general purpose

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

**Absolute maximum ratings(Ta=25℃)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	1400	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	800	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		6	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25℃	80	W
T <sub>j</sub>	Junction temperature		150	℃
T <sub>stg</sub>	Storage temperature		-55~150	℃

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =10mA; I <sub>B</sub> =0	800			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.5A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =2.5A; I <sub>B</sub> =0.5A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =1200V; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =7V; I <sub>C</sub> =0			100	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =2.5A; V <sub>CE</sub> =4V	6			
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =0.5A; V <sub>CE</sub> =12V		4		MHz

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PACKAGE OUTLINE

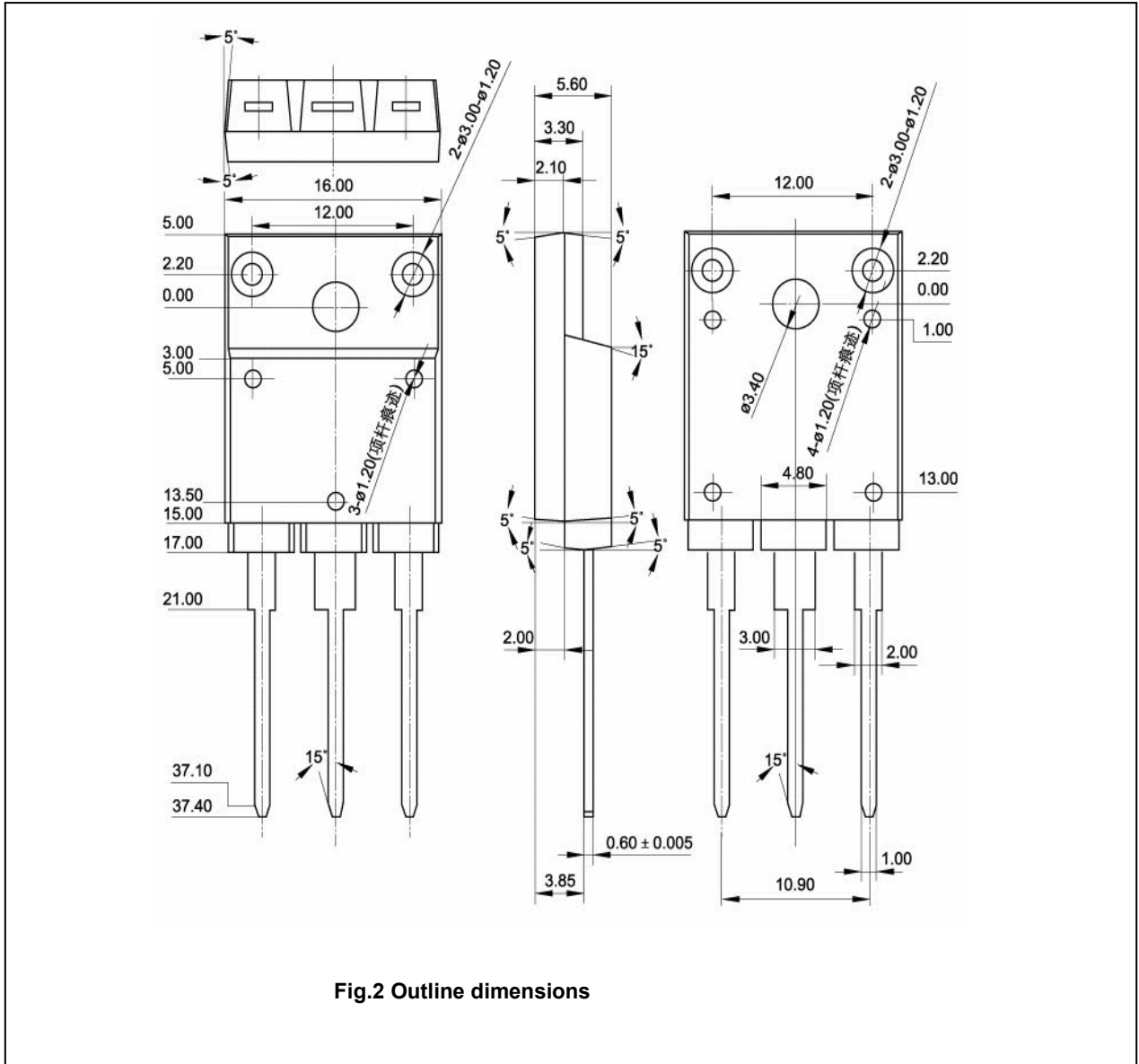


Fig.2 Outline dimensions